



ATTORNEY DOCKET NO. 43890-449
PATENT

#9/Comdt B
Apr 16/02
14/19/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Hidenori KAMEI, et al.
Serial No.: 09/680,943
Filed: October 10, 2000
For: P-TYPE NITRIDE SEMICONDUCTOR AND
METHOD OF MANUFACTURING THE SAME)

) Group Art Unit: 2823
Examiner: DEVEN M. COLLINS

AMENDMENT UNDER 37 C.F.R. § 1.111

Hon. Assistant Commissioner for Patents
Washington, DC 20231

Sir:

In response to the Office Action dated January 16, 2002, having a shortened statutory period for response set to expire April 16, 2002, please amend the above-identified application as follows:

IN THE CLAIMS:

Please cancel claim 5, without prejudice.

Please amend claim 1 and add new claims 13 and 14 as follows:

1. (Amended) A method for manufacturing p-type nitride semiconductor

comprising:

a semiconductor layer forming process for forming a (low resistivity) p-type nitride

B1

RECEIVED
APR 17 2002
TECHNOLOGY CENTER 2800